ABSTRACT OF THE DISCLOSURE

The invention provides a method of programming in a nonvolatile semiconductor memory device, having a plurality of memory cell strings connected to a plurality of bitlines
5   and constructed of a plurality of memory cell transistors whose gates are coupled to a plurality of wordlines, and a plurality of registers corresponding to the bitlines. The method involves applying a first voltage to a first one of the bitlines and applying a second voltage to a second one of the bitline, the first bitline being adjacent to the second bitline, the first and second voltages being supplied from the registers; electrically isolating the first and second
10   bitlines from their corresponding registers; charging the first bitline up to a third voltage higher than the first voltage and lower than the second voltage; and applying a fourth voltage to a wordline after cutting off current paths into the first and second bitlines.